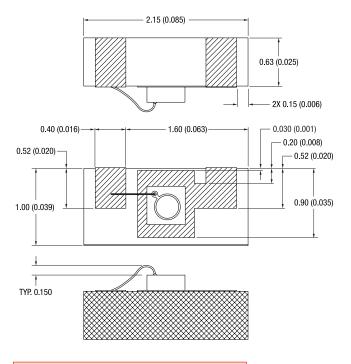
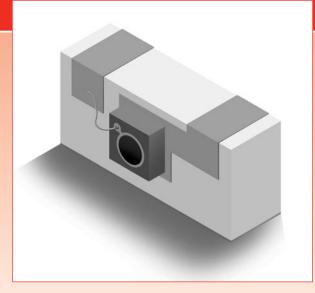
■FCI-InGaAs-XXX-WCER

High Speed InGaAs Photodiodes Mounted on Wraparound Ceramic Packages

FCI-InGaAs-XXX-WCER with active area sizes of 70µm, 120µm, 300µm, 400μm and 500μm are part of a line of monitor photodiodes mounted on metallized ceramic substrates. These compact assemblies are designed for ease of integration. The chips can be epoxy or eutectic mounted onto the ceramic substrate.



- All units in millimeters (inches).
- \bullet All devices are eutectic mounted with tolerance of $\pm 50 \mu m.$



APPLICATIONS

- High Speed Optical Communications
- Gigabit Ethernet/Fibre Channel
- SONET / SDH, ATM
- Diode Laser Monitor
- Instrumentation

FEATURES

- Low Noise
- High Responsivity
- High Speed
- Spectral Range 900nm to 1700nm

Absolute Maximum Ratings											
PARAMETERS	SYMBOL	MIN	MAX	UNITS							
Storage Temperature	T _{stg}	-40	+85	°C							
Operating Temperature	T _{op}	0	+70	°C							
Soldering Temperature	T _{sld}		+260	°C							

Electro-Optical Characteristics T _A =23°C																		
PARAMETERS	SYMBOL	CONDITIONS	FCI-InGaAs-70WCER		FCI-InGaAs-120WCER		FCI-InGaAs-300WCER		FCI-InGaAs-400WCER			FCI-InGaAs-500WCER			UNITS			
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIIS
Active Area Diameter	AA_{ϕ}			70			120			300			400			500		μm
Responsivity	R _λ	λ=1310nm	0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		0.80	0.90		A/W
	N _λ	λ=1550nm	0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		0.90	0.95		
Capacitance	C _j	V _R = 5.0V		0.65			1.0			10.0			14.0			20.0		pF
Dark Current	I _d	V _R = 5.0V		0.03	2		0.05	2		0.30	5		0.40	5		0.50	20	nA
Rise Time/ Fall Time	t _r /t _f	$V_R = 5.0V,$ $R_L = 50\Omega$ 10% to 90%			0.20			0.30			1.5			3.0			10.0	ns
Max. Revervse Voltage					20			20			15			15			15	V
Max. Reverse Current					1			2			2			2			2	mA
Max. Forward Current					5			5			8			8			8	mA
NEP				3.44E- 15			4.50E- 15			6.28E- 15			7.69E- 15			8.42E- 15		W/√Hz